

**REMARKS**

Claims 1, 5 and 7-16 are pending in this application. Claims 7-16 have been withdrawn from consideration. By this Amendment, claims 1 and 5 are amended and claims 2-4 and 6 are canceled. No new matter is added by this Amendment. Support for added claim language can be found in the specification. See, e.g., page 11, lines 2-14.

**I. Rejoinder**

Because claims 7-16 depend from elected claim 1, or otherwise include all of the limitations of claim 1, upon allowance of claim 1, rejoinder and allowance of withdrawn claims 7-16 is requested. See MPEP §821.04(b).

**II. Claim Rejections-35 U.S.C. §102(b) and §103**

Claims 1 and 3-6 are rejected under 35 U.S.C. §102(b) over U.S. Patent No. 5,378,382 (Nishimura); and claim 2 is rejected under 35 U.S.C. §103(a) over Nishimura in view of EP Patent Application No. EP 1 039 525 (Nabatame). These rejections are respectfully traversed.

In the present application, claim 1 recites, *inter alia*, a ferroelectric material comprising an A-site compensation component and a B-site compensation component, each of which comprises an oxide material including at least Si and Ge. The A-site compensation component constitutes an element which becomes divalent and an element which becomes trivalent, and the B-site compensation component constitutes an element which becomes pentavalent.

This means that each of the A-site compensation component and the B-site compensation component comprises a combination of an oxide material including at least Si and Ge (the first compensation component) and elements with different valence (the second compensation component). In accordance with the present invention, crystallization may be performed at a low temperature by using the first compensation components when the second compensation components are sufficiently added to lead zirconate titanate (PZT) to compensate for the vacancy of the A-site or B-site. (See page 16, lines 2-14 of the present

specification). Therefore, the present invention accommodates manufacture of a ferroelectric film, which has a preferable crystal structure and compensates for the vacancy of the A-site or B-site at a low temperature.

In contrast, Nishimura and Nabatame fail to teach each of the A-site compensation component and the B-site compensation component being a combination of the first and second compensation components. For the foregoing reasons, claim 1, as well as claims depending therefrom, are not anticipated or otherwise rendered obvious by Nishimura or Nabatame.

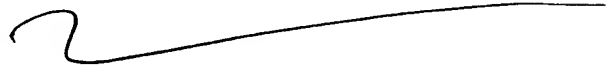
Withdrawal of the rejections is respectfully requested.

**III. Conclusion**

In view of the foregoing, it is respectfully submitted that this application is in condition for allowance. Favorable reconsideration and prompt allowance of the pending claims are earnestly solicited.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number set forth below.

Respectfully submitted,



James A. Oliff  
Registration No. 27,075

Eric D. Morehouse  
Registration No. 38,565

JAO:EDM/axl

Date: October 30, 2006

**OLIFF & BERRIDGE, PLC**  
**P.O. Box 19928**  
**Alexandria, Virginia 22320**  
**Telephone: (703) 836-6400**

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